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Renowned Memory Expert Joins Innovative Silicon

Dr. Wolfgang Mueller to lead Z-RAM device engineering and process integration efforts

SANTA CLARA, Calif. — June 19, 2009 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory (FB) technology, today announced that Dr. Wolfgang Mueller has joined ISi as director, device engineering and process integration. Mueller, a 30-year industry veteran, has spearheaded a number of memory innovations including the development and implementation of "buried wordline" DRAM technology at Qimonda AG. Dr. Mueller is reporting to Michael Van Buskirk, senior vice president, engineering and operations.

"We are thrilled that Dr. Mueller has joined ISi," said Van Buskirk. "Dr. Mueller brings a unique perspective to ISi because he has achieved significant breakthroughs in conventional DRAMs and he has a broad understanding of emerging memory technologies. He will be a key contributor as we continue to scale Z-RAM to sub-40nm DRAM process technologies."

Prior to joining ISi, Dr. Mueller served as Qimonda Fellow of DRAM Technology at Qimonda AG. During his tenure at Qimonda, Dr. Mueller led the development team that transitioned Qimonda from trench capacitors to stacked capacitors, led the concept team that developed Qimonda's buried wordline technology, and led the concept team working on the $4F^2$ DRAM bit cell. Recently, Dr. Mueller focused on investigating successors to conventional one-transistor, one-capacitor DRAM, and most recently, researched floating body memory structures. He has presented at numerous industry conferences and has authored more than 50 papers and 20 patents. Dr. Mueller received his Ph.D. in electronic engineering from Vienna University of Technology in Vienna, Austria.

About Innovative Silicon

Innovative Silicon, Inc. (ISi) licenses its Z-RAM® ultra-dense memory technology to stand-alone DRAM manufacturers so they may manufacture the lowest-cost, most-advanced memory ICs. Licensees include Hynix Semiconductor for use in its DRAM chips, and AMD for use in microprocessors. The heart of the Z-RAM technology is the "zero-capacitor," single-transistor floating-body bit-cell that eliminates the complex capacitor found in today's DRAM technologies – making Z-RAM the world's lowest-cost and most-scalable memory technology. Since 2003, the company has closed $47 million in venture capital funding, received numerous industry awards such as *IEEE Spectrum Magazine's* "2007 Emerging

Technology Most Likely to Succeed," been granted dozens of patents, and established global R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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